

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
22	BRS	1	electric adj field adj reducing adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/12 16:00		
23	BRS	1424	(electric adj field) near10 (reduc\$6 near10 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/12 16:02		
24	BRS	321	electric adj field adj relaxation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 04:08		
25	BRS	305	(kozuka near2 hiraki) or (sugawa near2 shigetoshi)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:57		
26	BRS	37	((kozuka near2 hiraki) or (sugawa near2 shigetoshi)) and (electric adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 06:52		
27	BRS	27	(hole and electron) adj (injection) adj (inhibiting or blocking) adj (layer or region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:34		
28	BRS	17	((injection) adj (inhibiting or blocking) adj (layer or region)) and ((conduction and valence) adj band)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:51		
29	BRS	168	level near10 equal near10 ((valence or conduction) adj band)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:51		
30	BRS	1	6127692.URPN.	USPAT	2002/12/13 07:52		
31	BRS	11	((kozuka near2 hiraki) or (sugawa near2 shigetoshi)) and (valence and conduction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:58		
32	BRS	11	((kozuka near2 hiraki) or (sugawa near2 shigetoshi)) and ((valence and conduction) near2 band)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 08:08		
33	BRS	15	("4169273" "4571624" "4745488" "5043719" "5060040" "5233442" "5262850" "5272548" "5288988" "5317406" "5335094" "5420452" "5463420" "5812109" "5999150"),PN.	USPAT	2002/12/13 08:11		
34	BRS	0	canon and (electron adj injection adj inhibiting) and (valence adj band)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 08:21		
35	BRS	4	canon and (electron adj injection adj inhibiting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 11:48		
36	BRS	0	(monocrystalline and polycrystalline and microcrystalline) near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 11:50		
37	BRS	134	(monocrystalline and polycrystalline) near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 11:54		
38	BRS	677	(microcrystalline) near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:10		
39	BRS	27	((monocrystalline) near10 substrate) and 348/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 11:55		
40	BRS	2	((microcrystalline) near10 substrate) and 348/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 11:55		
41	BRS	45	((polycrystalline) near10 substrate) and 348/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 11:55		
42	BRS	265	(microcrystalline near10 silicon) near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:19		
43	BRS	47	(microcrystalline near10 silicon near10 polycrystalline) near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:20		